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INFORMATION DISCLOSURE								First Named Inventor		Chakravarthi et al.	<u>∞</u> ⊒		
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A	CA	"Modeling Solid Source Boron Diffusion for Advanced Transistor Applications", P. PACKAN, S. THOMPSON, E. ANDIDEH,											
- YY		S. YU, M. GILES, J SANDFORD and M. BOHR, 1998 IEEE, IEDM 98-505, 4 Pages.											

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M	CA	"Modeling Solid Source Boron Diffusion for Advanced Transistor Applications", P. PACKAN, S. THOMPSON, E. ANDIDEH, S. YU, M. GILES, J SANDFORD and M. BOHR, 1998 IEEE, IEDM 98-505, 4 Pages.	
W.	СВ	"Effect of fluorine on the diffusion of boron in ion implanted Si", Applied Physics Letters, 1998 American Institute of Physics, DANIEL F, DOWNEY, JUDY W. CHOW, EMI ISHIDA and KEVIN S. JONES, Volume 73, Number 9, August 31, 1998, 3 Pages.	
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